

ABSTRACT OF THE DISCLOSURE

A semiconductor light emitter includes a quantum well active layer which includes nitrogen and at least one other Group-V element, and barrier layers which are provided alongside the quantum well active layer, wherein the quantum well active layer and the barrier layers together constitute an active layer, wherein the barrier layers are formed of a Group-III-V mixed-crystal semiconductor that includes nitrogen and at least one other Group-V element, a nitrogen composition thereof being smaller than that of the quantum well active layer.